

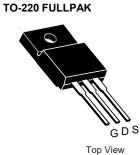
# K40A06N1-VB Datasheet N-Channel 60-V (D-S) MOSFET

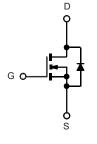
PRODUCT	SUMMARY	
V <sub>DS</sub> (V)	<b>R<sub>DS(on)</sub> (</b> Ω)	I <sub>D</sub> (A) <sup>a</sup>
60	0.010 at V <sub>GS</sub> = 10 V	70
00	0.012 at V <sub>GS</sub> = 4.5 V	55

#### FEATURES

- 175 °C Junction Temperature
- Trench Power MOSFET
- Material categorization:







N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T <sub>C</sub> = 25	5 °C, unless otherv	vise noted)			
Parameter		Symbol	Limit	Unit	
Gate-Source Voltage		V <sub>GS</sub>	± 20	V	
Continuous Drain Current (T 175 °C)h	T <sub>C</sub> = 25 °C	L_	70		
Continuous Drain Current (T <sub>J</sub> = 175 °C) <sup>b</sup>	T <sub>C</sub> = 100 °C		50 <sup>a</sup>		
Pulsed Drain Current		I <sub>DM</sub>	200	A	
Continuous Source Current (Diode Conduction)		I <sub>S</sub>	50ª		
Avalanche Current		I <sub>AS</sub>	50		
Single Avalanche Energy (Duty Cycle $\leq$ 1 %)	L = 0.1 mH	E <sub>AS</sub>	125	mJ	
Maximum Power Dissipation	T <sub>C</sub> = 25 °C	P <sub>D</sub>	136	W	
	T <sub>A</sub> = 25 °C		3 <sup>b</sup> , 8.3 <sup>b, c</sup>	- vv	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to 175	°C	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum lumation to Ambient?	t ≤ 10 sec	R <sub>thJA</sub>	15	18	
Maximum Junction-to-Ambient <sup>a</sup>	Steady State	I <b>™</b> thJA	40	50	°C/W
Maximum Junction-to-Case		$R_{thJC}$	0.85	1.1	

Notes:

a. Package limited.

b. Surface mounted on 1" x 1" FR4 board.

 $c. \ t \leq 10 \ s.$ 

Parameter	Symbol	Test Conditions	Min.	Typ.ª	Max.	Unit	
Static				•	L1		
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS}$ = 0 V, I <sub>D</sub> = 250 µA	60			V	
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}$ , $I_D = 250 \ \mu A$	1	2	3	v	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 V, V_{GS} = \pm 20 V$			± 100	nA	
		V <sub>DS</sub> = 60 V, V <sub>GS</sub> = 0 V			1		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS}$ = 60 V, $V_{GS}$ = 0 V, $T_{J}$ = 125 °C			50	μA	
		$V_{DS}$ = 60 V, $V_{GS}$ = 0 V, $T_{J}$ = 175 °C			250		
On-State Drain Current⁵	I <sub>D(on)</sub>	V <sub>DS</sub> = 5 V, V <sub>GS</sub> = 10 V	60			А	
		V <sub>GS</sub> = 10 V, I <sub>D</sub> = 20 A		0.010			
		$V_{GS}$ = 10 V, I <sub>D</sub> = 20 A, T <sub>J</sub> = 125 °C		0.016		0	
Drain-Source On-State Resistance <sup>b</sup>	R <sub>DS(on)</sub>	$V_{GS}$ = 10 V, I <sub>D</sub> = 20 A, T <sub>J</sub> = 175 °C		0.020		- Ω	
		V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 15 A		0.012		1	
Forward Transconductance <sup>b</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 20 A		60		S	
Dynamic							
Input Capacitance	C <sub>iss</sub>			2650			
Output Capacitance	C <sub>oss</sub>	$V_{GS}$ = 0 V, $V_{DS}$ = 25 V, f = 1 MHz		470		Ω S pF nC	
Reverse Transfer Capacitance	C <sub>rss</sub>			225			
Total Gate Charge <sup>c</sup>	Qg			47	70		
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 10 V, I <sub>D</sub> = 50 A		10		nC	
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>			12			
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			10	20		
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DD}$ = 30 V, R <sub>L</sub> = 0.6 Ω I <sub>D</sub> ≅ 50 A, V <sub>GEN</sub> = 10 V, R <sub>g</sub> = 2.5 Ω		15	25	20	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>			35	50	- ns	
Fall Time <sup>c</sup>	t <sub>f</sub>			20	30		
Source-Drain Diode Ratings and Cha	aracteristics (	T <sub>C</sub> = 25 °C)		·			
Pulsed Current	I <sub>SM</sub>				70	А	
Diode Forward Voltage	V <sub>SD</sub>	I <sub>F</sub> = 20 A, V <sub>GS</sub> = 0 V		1	1.5	V	
Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 20 A, di/dt = 100 A/μs		45	100	ns	

Notes:

a. For design aid only; not subject to production testing.

b. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %.

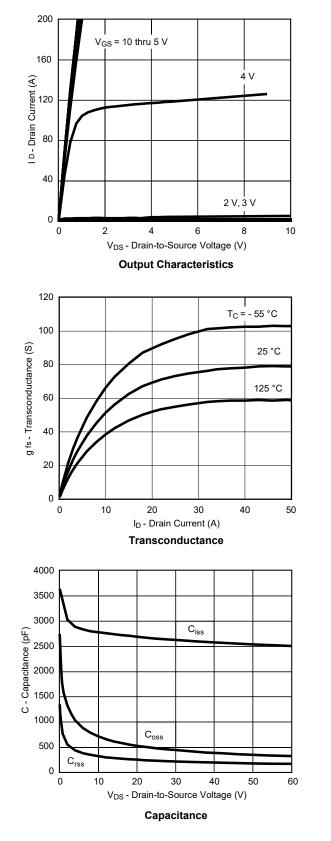
c. Independent of operating temperature.

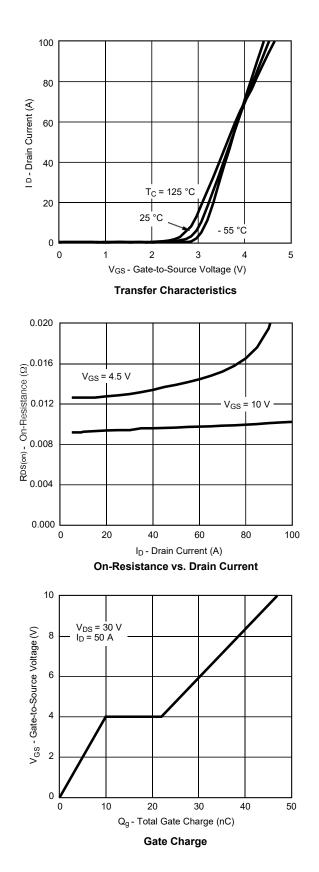
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

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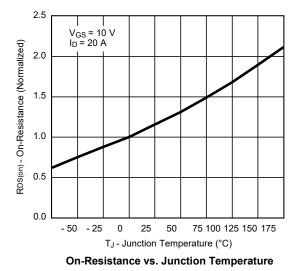
### TYPICAL CHARACTERISTICS (25 °C unless noted)







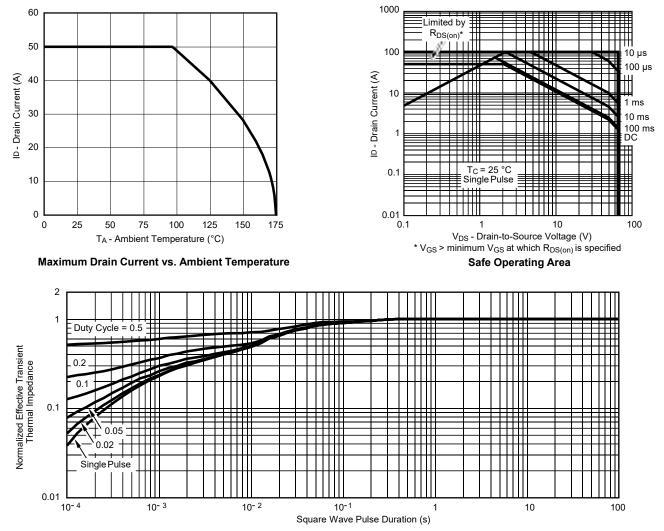
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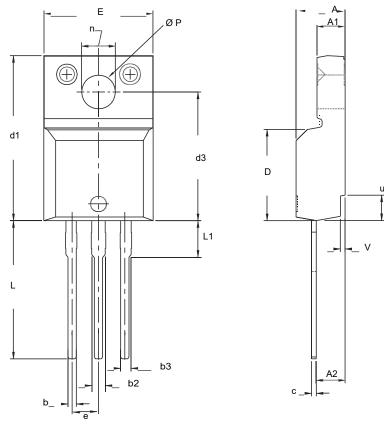
#### THERMAL RATINGS



Normalized Thermal Transient Impedance, Junction-to-Case



## **TO-220 FULLPAK (HIGH VOLTAGE)**



DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
А	4.570	4.830	0.180	0.190
A1	2.570	2.830	0.101	0.111
A2	2.510	2.850	0.099	0.112
b	0.622	0.890	0.024	0.035
b2	1.229	1.400	0.048	0.055
b3	1.229	1.400	0.048	0.055
С	0.440	0.629	0.017	0.025
D	8.650	9.800	0.341	0.386
d1	15.88	16.120	0.622	0.635
d3	12.300	12.920	0.484	0.509
E	10.360	10.630	0.408	0.419
е	2.54	BSC	0.100 BSC	
L	13.200	13.730	0.520	0.541
L1	3.100	3.500	0.122	0.138
n	6.050	6.150	0.238	0.242
ØP	3.050	3.450	0.120	0.136
u	2.400	2.500	0.094	0.098
V	0.400	0.500	0.016	0.020

#### Notes

1. To be used only for process drawing. 2. These dimensions apply to all TO-220, FULLPAK leadframe versions 3 leads. 3. All critical dimensions should C meet  $C_{pk} > 1.33$ . 4. All dimensions include burrs and plating thickness. 5. No chipping or package damage.



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